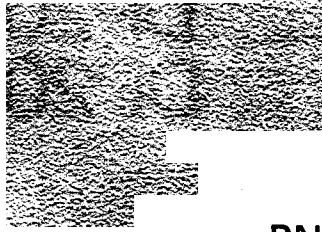
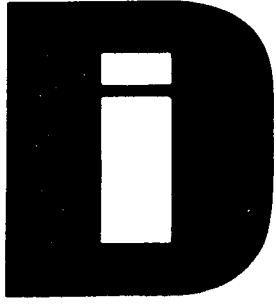


# DIONICS INC.

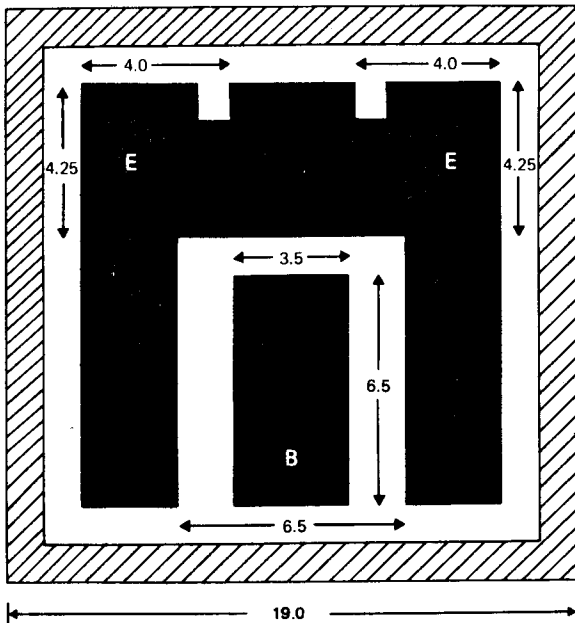
65 RUSHMORE ST., WESTBURY, N.Y. 11590 516•997•7474



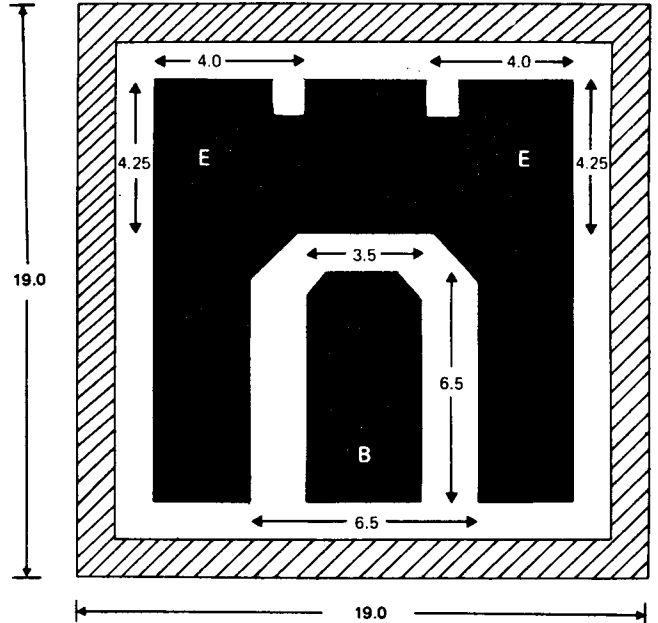
DP203 - DN203  
DP204 - DN204  
DP205 - DN205  
DP206 - DN206

SILICON  
PNP AND NPN COMPLEMENTARY  
HIGH VOLTAGE TRANSISTOR CHIPS  
DESIGNED FOR HYBRID CIRCUIT APPLICATIONS.

NPN



PNP



DN203  
DN204  
DN205  
DN206

DP203  
DP204  
DP205  
DP206

Dimensions in Mils



Aluminum



Oxide

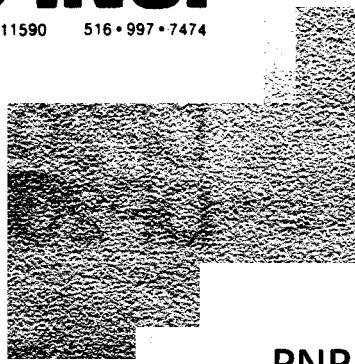
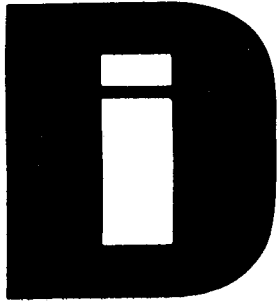


Silicon

- Chip Thickness=6 Mils  $\pm$ 1 Mil
- Min. Dimension Across Bonding Pads=3.5 Mils
- Min. Separation Between Bonding Pads=1.0 Mils
- Distance from Bonding Pads to Edge of Chips=2.5 Mils

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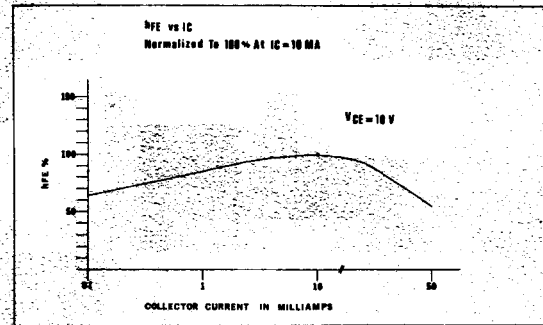
DP203 - DN203  
 DP204 - DN204  
 DP205 - DN205  
 DP206 - DN206

SILICON  
 PNP AND NPN COMPLEMENTARY  
 HIGH VOLTAGE TRANSISTOR CHIPS  
 DESIGNED FOR HYBRID CIRCUIT APPLICATIONS.

**APPLICATIONS:** PLASMA AND GAS DISCHARGE DISPLAY DRIVERS, HIGH VOLTAGE, COMPLEMENTARY SYMMETRY AMPLIFIERS, AND SWITCHING CIRCUITRY.

**ADVANTAGES:** HIGH VOLTAGE • HIGH GAIN • LOW LEAKAGE CURRENTS • OVERSIZED BONDING PADS •

The high efficiency parallel emitter construction provides improved beta retention at high current levels. The large area bonding pads are positioned for maximum flexibility of substrate layout. Unique surface stabilization processing results in lower leakage currents and prevents the beta degradation frequently encountered during the extended high temperature assembly operations required for complex hybrid circuit construction. Chips are gold backed for eutectic die-attach, and have aluminum bonding pads for all conventional wire bonding techniques.



← 100% Probe Tested to These Parameters @ 25°C → Guaranteed (tested on sample basis)

	$h_{FE} @$ $I_C=10mA$ $V_{CE}=10V$	$V_{CB0}$ Volts Min. @ $I_C=10\mu A$ $I_E=0$	$V_{CE0}$ Volts Min. @ $I_C=1.0mA$ $I_B=0$	$V_{EB0}$ Volts Min. @ $I_B=10\mu A$ $I_C=0$	$I_{CB0}$ nA Max. @ $V_{CB}$ as below $I_E=0$	$V_{CE} (SAT.)$ Volts Max. @ $I_C=10mA$ $I_B=1.0mA$	$C_{OB}$ pF Max. @ $V_{CB}=10V$ $I_E=0$ $f=100KHz$	$f_t$ MHz Min. @ $I_C=10mA$ $V_{CE}=10V$ $f=100MHz$
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DN203 DP203	40 MIN	200	200	5.0	100 @ 175V	5.0	8.0	50
DN204 DP204	40 MIN	175	175	5.0	100 @ 150V	5.0	8.0	50
DN205 DP205	40 MIN	150	150	5.0	100 @ 125V	5.0	8.0	50
DN206 DP206	40 MIN	125	125	5.0	100 @ 100V	5.0	8.0	50